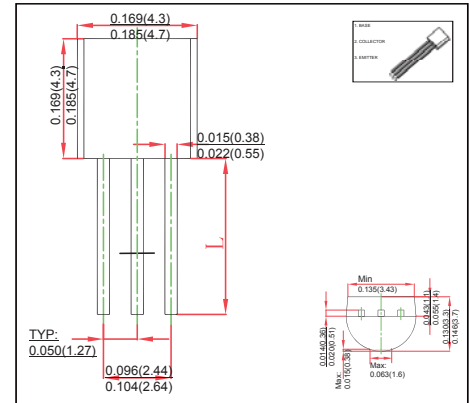


TO-92 Plastic-Encapsulate Transistors
FEATURE

- Power switching applications
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector -Base Voltage	VCBO	600	V
Collector-Emitter Voltage	VCEO	400	V
Emitter-Base Voltage	VEBO	7	V
Collector Current -Continuous	IC	0.2	A
Collector Power Dissipation	PC	0.75	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55 ~+150	°C

Electrical Specification(T_A=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	I _C = 100μA , I _B =0	600			V
Collector-emitter breakdown voltage	V(BR)CEO	I _C = 1mA , I _B =0	400			V
Emitter-base breakdown voltage	V(BR)EBO	I _E = 100μA , I _E =0	7			V
Collector cut-off current	ICBO	V _{CB} = 600V , I _E =0			100	μA
Collector cut-off current	ICEO	V _{CE} = 400V, I _B =0			200	μA
Emitter cut-off current	IEBO	V _{EB} = 400V, I _C =0			100	μA
DC current gain	hFE(1)	V _{CE} = 20V, I _C = 20mA	14		29	
	hFE(2)	V _{CE} = 10V, I _C = 0.25 mA	5			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 50mA, I _B = 10 mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 50 mA, I _B = 10mA			1.2	V
Transition frequency	f _t	V _{CE} = 20V, I _C =20mA f = 1MHz	8			
Fall time	t _f	I _C =50mA, I _{B1} =-I _{B2} =5mA,			0.3	μs
Storage time	t _s	V _{CC} =45V			1.5	μs